



PBSS5130T

30 V; 1 A PNP low V_{CEsat} (BISS) transistor

9 July 2013

Product data sheet

1. General description

PNP low V_{CEsat} Breakthrough In Small Signal (BISS) transistor in a small SOT23 Surface-Mounted Device (SMD) plastic package.

2. Features and benefits

- Small SMD plastic package
- Low collector-emitter saturation voltage V_{CEsat}
- High collector current capability: I_C and I_{CM}
- Higher efficiency due to less heat generation
- AEC-Q101 qualified

3. Applications

- DC-to-DC conversion
- Supply line switching
- Battery charger
- LCD backlighting
- Driver in low supply voltage applications (e.g. lamps and LEDs)

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{CEO}	collector-emitter voltage	open base	-	-	-30	V
I_C	collector current		-	-	-1	A
I_{CM}	peak collector current	single pulse; $t_p \leq 1$ ms	-	-	-3	A
R_{CEsat}	collector-emitter saturation resistance	$I_C = -500$ mA; $I_B = -50$ mA; pulsed; $t_p \leq 300$ μ s; $\delta \leq 0.02$; $T_{amb} = 25$ °C	-	-	220	m Ω

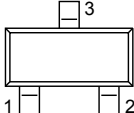
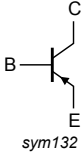


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5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	B	base	 TO-236AB (SOT23)	 sym132
2	E	emitter		
3	C	collector		

6. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
PBSS5130T	TO-236AB	plastic surface-mounted package; 3 leads	SOT23

7. Marking

Table 4. Marking codes

Type number	Marking code [1]
PBSS5130T	%3E

[1] % = placeholder for manufacturing site code

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V _{CBO}	collector-base voltage	open emitter		-	-30	V
V _{CEO}	collector-emitter voltage	open base		-	-30	V
V _{EBO}	emitter-base voltage	open collector		-	-5	V
I _C	collector current			-	-1	A
I _{CM}	peak collector current	single pulse; t _p ≤ 1 ms		-	-3	A
I _{BM}	peak base current			-	-300	mA
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C	[1]	-	300	mW
			[2]	-	480	mW
T _j	junction temperature			-	150	°C
T _{amb}	ambient temperature			-55	150	°C
T _{stg}	storage temperature			-65	150	°C

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm².

9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
R _{th(j-a)}	thermal resistance from junction to ambient	in free air	[1]	-	-	417	K/W
			[2]	-	-	260	K/W

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm².

10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
I_{CBO}	collector-base cut-off current	$V_{CB} = -30\text{ V}; I_E = 0\text{ A}; T_{amb} = 25\text{ }^{\circ}\text{C}$	-	-	-100	nA
		$V_{CB} = -30\text{ V}; I_E = 0\text{ A}; T_j = 150\text{ }^{\circ}\text{C}$	-	-	-50	μA
I_{EBO}	emitter-base cut-off current	$V_{EB} = -4\text{ V}; I_C = 0\text{ A}; T_{amb} = 25\text{ }^{\circ}\text{C}$	-	-	-100	nA
h_{FE}	DC current gain	$V_{CE} = -2\text{ V}; I_C = -100\text{ mA}; \text{pulsed}; t_p \leq 300\text{ }\mu\text{s}; \delta \leq 0.02; T_{amb} = 25\text{ }^{\circ}\text{C}$	300	450	-	
		$V_{CE} = -2\text{ V}; I_C = -500\text{ mA}; \text{pulsed}; t_p \leq 300\text{ }\mu\text{s}; \delta \leq 0.02; T_{amb} = 25\text{ }^{\circ}\text{C}$	260	350	-	
		$V_{CE} = -2\text{ V}; I_C = -1\text{ A}; \text{pulsed}; t_p \leq 300\text{ }\mu\text{s}; \delta \leq 0.02; T_{amb} = 25\text{ }^{\circ}\text{C}$	210	290	-	
V_{CEsat}	collector-emitter saturation voltage	$I_C = -100\text{ mA}; I_B = -1\text{ mA}; \text{pulsed}; t_p \leq 300\text{ }\mu\text{s}; \delta \leq 0.02; T_{amb} = 25\text{ }^{\circ}\text{C}$	-	-	-100	mV
		$I_C = -1\text{ A}; I_B = -50\text{ mA}; \text{pulsed}; t_p \leq 300\text{ }\mu\text{s}; \delta \leq 0.02; T_{amb} = 25\text{ }^{\circ}\text{C}$	-	-	-225	mV
R_{CEsat}	collector-emitter saturation resistance	$I_C = -500\text{ mA}; I_B = -50\text{ mA}; \text{pulsed}; t_p \leq 300\text{ }\mu\text{s}; \delta \leq 0.02; T_{amb} = 25\text{ }^{\circ}\text{C}$	-	-	220	m Ω
V_{BEsat}	base-emitter saturation voltage	$I_C = -2\text{ A}; I_B = -200\text{ mA}; \text{pulsed}; t_p \leq 300\text{ }\mu\text{s}; \delta \leq 0.02; T_{amb} = 25\text{ }^{\circ}\text{C}$	-	-	-1.1	V
V_{BEon}	base-emitter turn-on voltage	$V_{CE} = -2\text{ V}; I_C = -100\text{ mA}; \text{pulsed}; t_p \leq 300\text{ }\mu\text{s}; \delta \leq 0.02; T_{amb} = 25\text{ }^{\circ}\text{C}$	-	-	-0.75	V
f_T	transition frequency	$V_{CE} = -10\text{ V}; I_C = -100\text{ mA}; f = 100\text{ MHz}; T_{amb} = 25\text{ }^{\circ}\text{C}$	100	200	-	MHz
C_c	collector capacitance	$V_{CB} = -10\text{ V}; I_E = 0\text{ A}; i_e = 0\text{ A}; f = 1\text{ MHz}; T_{amb} = 25\text{ }^{\circ}\text{C}$	-	-	28	pF

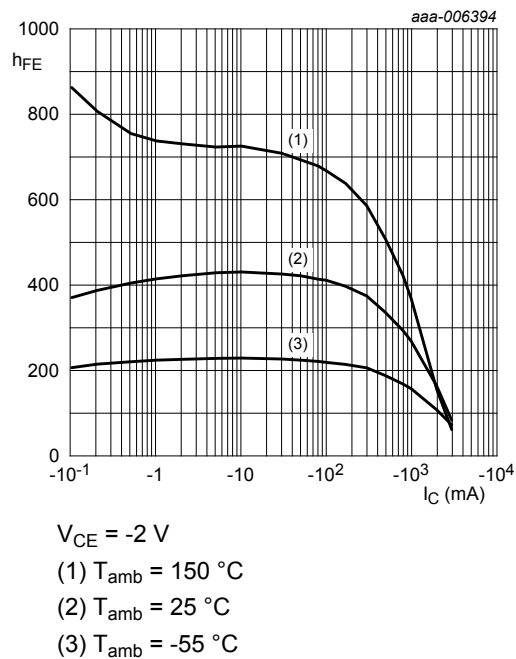


Fig. 1. DC current gain as a function of collector current; typical values

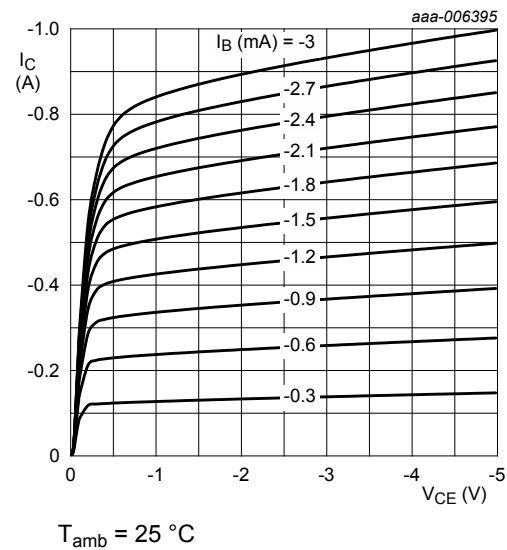


Fig. 2. Collector current as a function of collector-emitter voltage; typical values

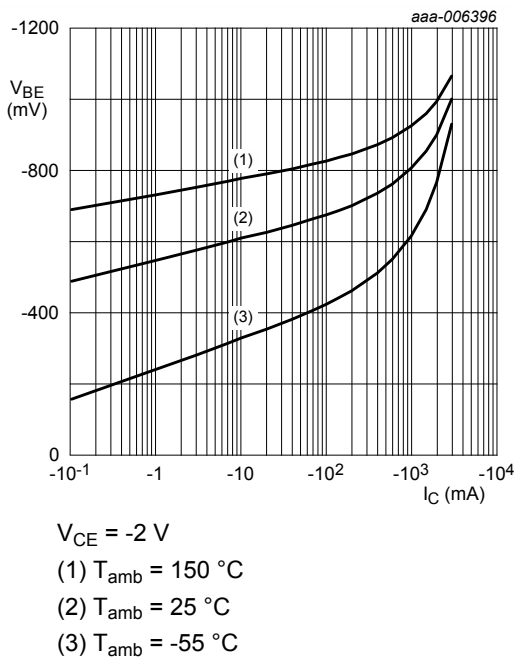


Fig. 3. Base-emitter voltage as a function of collector current; typical values

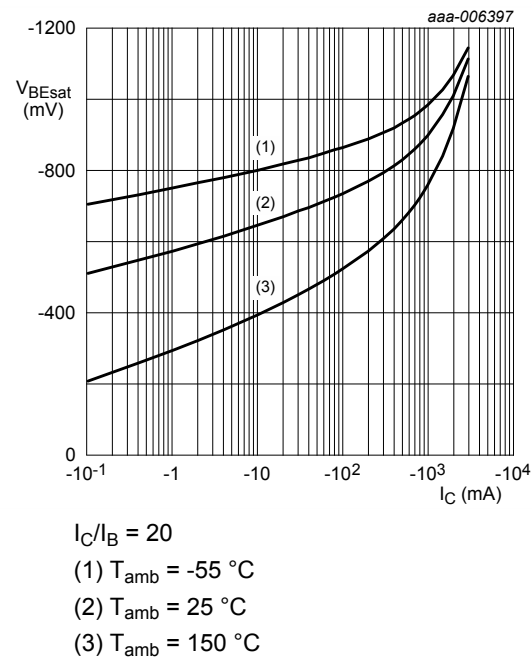


Fig. 4. Base-emitter saturation voltage as a function of collector current; typical values

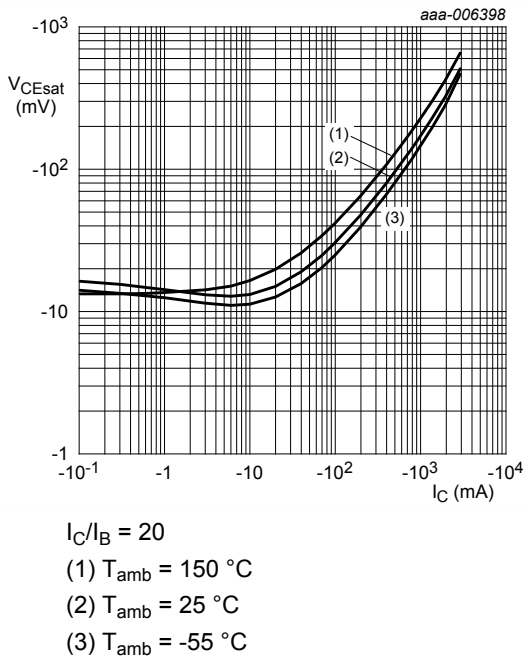


Fig. 5. Collector-emitter saturation voltage as a function of collector current; typical values

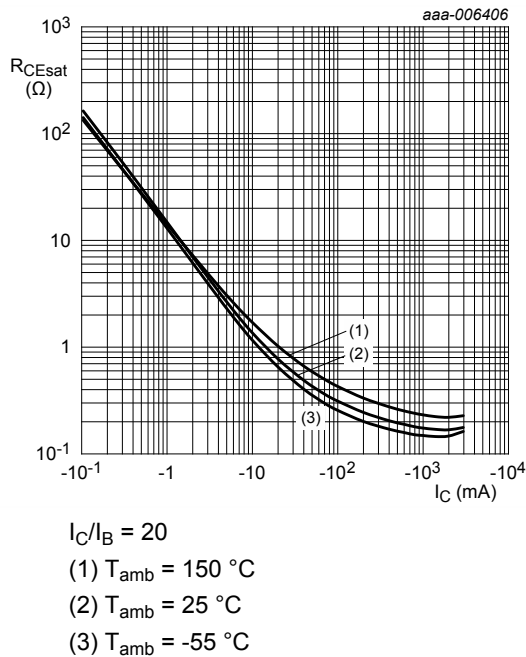


Fig. 6. Collector-emitter saturation resistance as a function of collector current; typical values

11. Test information

11.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard Q101 - Stress test qualification for discrete semiconductors, and is suitable for use in automotive applications.

12. Package outline

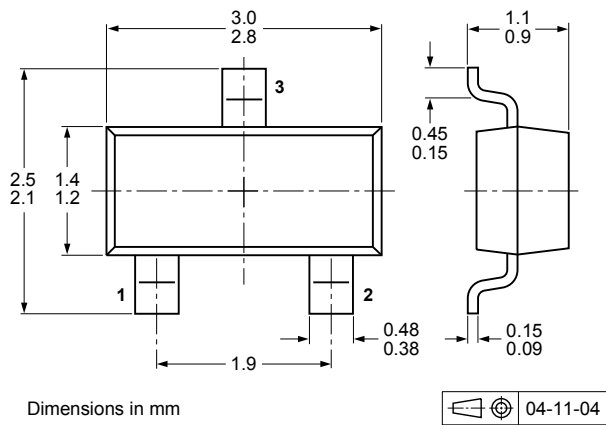


Fig. 7. Package outline TO-236AB (SOT23)

13. Soldering

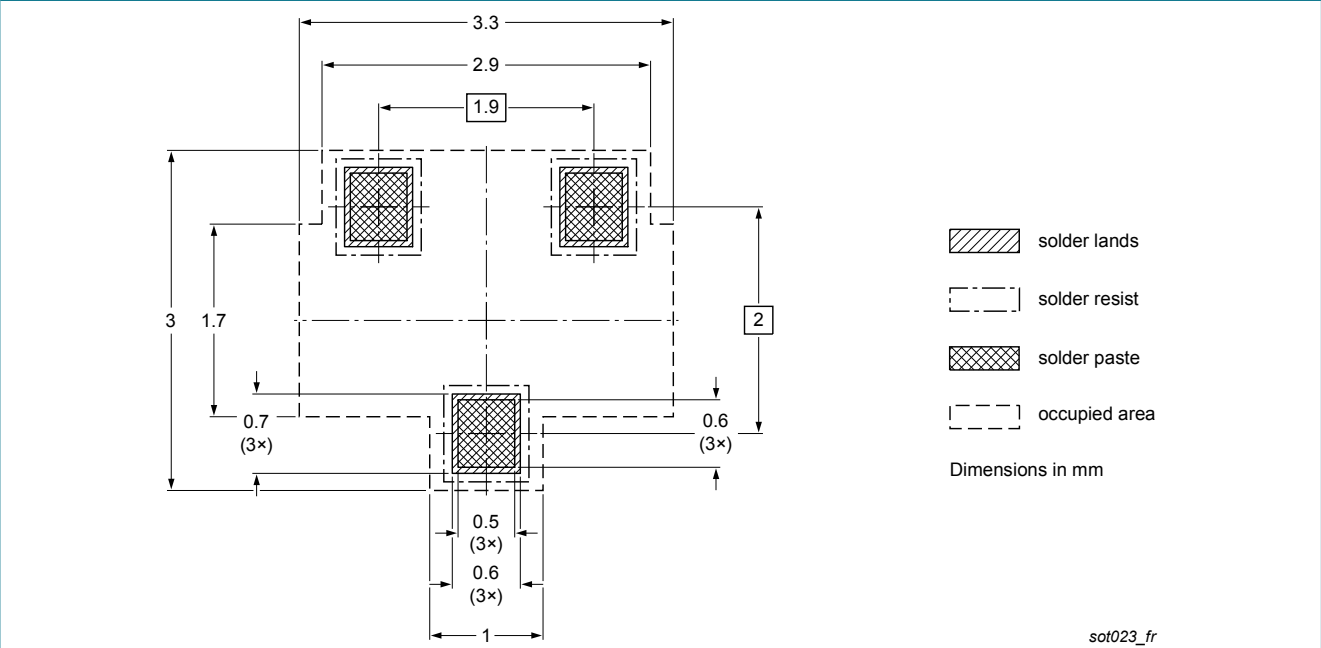


Fig. 8. Reflow soldering footprint for TO-236AB (SOT23)

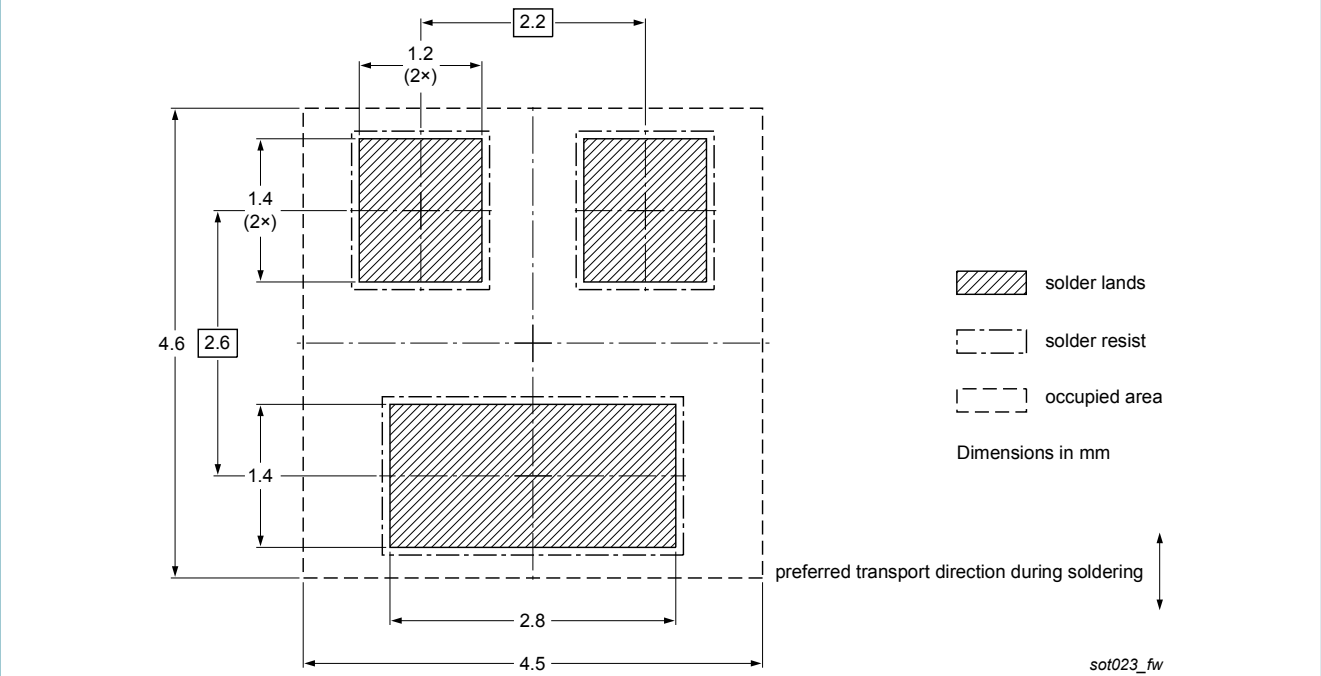


Fig. 9. Wave soldering footprint for TO-236AB (SOT23)

14. Revision history

Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PBSS5130T v.2	20130709	Product data sheet	-	PBSS5130T v.1
Modifications:	• The format of this document has been redesigned to comply with the new identity guidelines of NXP Semiconductors. • Legal texts have been adapted to the new company name where appropriate. • Sections "General description", "Features and benefits" and "Applications": updated • Section "Marking": updated • Table "Limiting values": ambient temperature T_{amb} updated • Table "Characteristics": base-emitter saturation voltage V_{BEsat} added • Figures 1 to 6: added • Section "Test information": added • Figure "Package outline TO-236AB (SOT23)": replaced by minimized outline drawing • Section "Soldering": added • Section "Legal information": updated			
PBSS5130T v.1	20031212	Product data sheet	-	-

15. Legal information

15.1 Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions".
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